Basic Course Information	01005143	Subject Category	Elective (M)	1
Course Number Class Format	Lecture	Credit Type and Number of Credits	Liective IV0	
Department Period of Study	Mechatronics	Student Category	Year 5	1
Required Materials	Semester 2 TBA	Classes per Week	1	1
nstructor Course Objective	Hitoshi Nishizawa	Jirapat Anuntahirunra		J
The course provides students with k topic covered in this course. Wide Ba Nano electronics, and Image Devices.			Silcon and SiGe Devices.	
Evaluation (Rubric)	Ideal Level of Achievement (Very Good)	Standard Level of Achievement (Good)	Unacceptable Level of Achievement (Fail)]
Physics of wide band gap devices	Able to describe how wide band gap devices work in	Able to describe how wide band gap	Cannot describe how wide band gap devices work.	
Physics of high frequency devices	detail Able to describe how high frequency devices work in	wide band gap devices work, Able to describe how high frequency	Cannot describe how high frequency devices work.	1
Physics of power semiconductor devices	Able to describe how power semiconductor devices work		Cannot describe how power semiconductor devices work.]
M(2) Ability to design, propose an	Relationship with Learnin	g Outcomes		-
Please change Please change				-
Teaching Method]
Dutline: Diase Format: Please Note :		Lecture and group work Lecture and group work		_
	Students are require	d to ask any questions after	r sufficient self-learning	1
Course Plan Semester 2	Contents and Met	hod of Course	Goals	Related MCC
1st Week	Operation of power semicor		Can explain how power semiconductor devices operate.	
			operate.	
-			Can explain how power	-
2nd Week	Applications and classificati semiconductors	on of power	can explain how power semiconductors are used in the society.	
3rd Week 4th Week		Power semiconductor wafers and manufacturing processes		
	processes			
				L
	Development of silicon power semiconductors. IGBT		Can explain the recent technology trend of develoing silicon-based power semiconductor	
			power semiconductor devices.	
5th Week	Wide band gap devices usin	ig SIC and GaN	Can explain the benefits and features of wide band gap devices using SiC and GaN.	
6th Week	National Holiday	National Holiday		
			Can explain how power semiconductor devices	
7th Week	Power semiconductors and	Power semiconductors and the decarbonization era		
8th Week	Preparing for Mid-term examination		Review problems for the mid term examination.	
				-
9th Week	National Holiday	National Holiday		
10th Week	Mid-term examination		Can slove problems at the mid-term examination.	
TOUT WEEK	mer territisseriingbon		mid-term examination.	
			Review and summarize the learning, can explain the how CCD and other image devices work.	
11th Week	Return exam papers and fe devices, CCD	Return exam papers and feedback / Image devices, CCD		
				-
12th Week	ferahertz technologies	Terahertz technologies		
	-			
13th Week	SiGe technology	SiGe technology		
				
14th Week	Nancelectronics		Can explain the outline of nanoelectronics.	
15th Week	Solid electrolyte devices	Solid electrolyte devices		
16th Week	Solid-state gas sensors		Can explain an application of solid-state gas sensors.	
17th Week	National Holiday			
			Beview related circuit	
18th Week Preparing for final examination		lon	problems for the final examination.	
				L
19th Week	Final Examination		Can slove problems at the final examination,	
	1		1	
204 14 1	Deture ever	and an also	Review and summarize the learning.	
20th Week	Return exam papers and fe	edback	Review and summarize the learning.	
20th Week	Return exam papers and fe	adback	Review and summarize the learning.	Do